# SENSITRON

Technical Data Data Sheet 501, Rev.-

# SILICON SCHOTTKY RECTIFIER DIE Very Low Forward Voltage Drop

## **Applications:**

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

#### Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

#### Maximum Ratings<sup>(1)</sup>:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V <sub>RWM</sub>	-	30	V
Max. Average Forward	I <sub>F(AV)</sub>	50% duty cycle, rectangular	3	А
Current		wave form		
Max. Peak One Cycle Non-	I <sub>FSM</sub>	8.3 ms, half Sine wave <sup>(1)</sup>	55	А
Repetitive Surge Current				
Non-Repetitive Avalanche	E <sub>AS</sub>	$T_{J} = 25 \ ^{\circ}C, I_{AS} = 1.3 \ A,$	5.6	mJ
Energy		L = 6.7 mH		
Repetitive Avalanche Current	I <sub>AR</sub>	$I_{AS}$ decay linearly to 0 in 1 $\mu$ s	1.3	А
		f limited by $T_J \max V_A = 1.5 V_R$		
Max. Junction Temperature	TJ	-	-65 to +150	°C
Max. Storage Temperature	T <sub>stg</sub>	-	-65 to +150	°C

## **Electrical Characteristics**<sup>(1)</sup>:

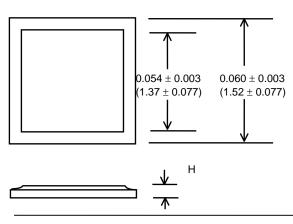
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V <sub>F1</sub>	@ 3A, Pulse, T <sub>J</sub> = 25 °C	0.49	V
	V <sub>F2</sub>	@ 3A, Pulse, T <sub>J</sub> = 125 °C	0.39	V
Max. Reverse Current	I <sub>R1</sub>	$@V_R = 30V$ , Pulse,	400	μΑ
		$T_J = 25 \ ^{\circ}C$		
	I <sub>R2</sub>	$@V_R = 30V$ , Pulse,	20	mA
		T <sub>J</sub> = 125 °C		
Max. Junction Capacitance	CT	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C	220	pF
		f <sub>SIG</sub> = 1MHz,		
		$V_{SIG} = 50 \text{mV} (\text{p-p})$		

(1) in SHD package

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#### Mechanical Dimensions: In Inches / mm

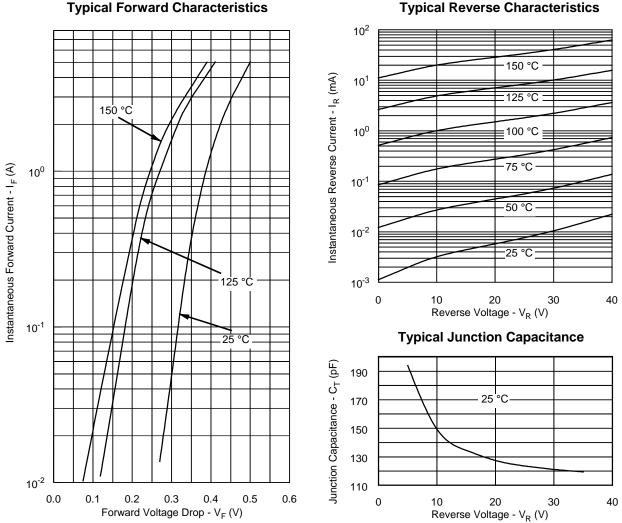


Bottom side metalization Ag - 30 kÅ minimum.

Top side metalization AI - 25 kÅ minimum or Ag - 30 kÅ minimum.

Bottom side is cathode, top side is anode.

Dimension H = 0.0105 ± 0.001 (0.27  $\pm$  0.026) for Al top; Dimension H = 0.0155 ± 0.001 (0.39  $\pm$  0.026) for Ag top.





#### **TECHNICAL DATA**

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